

350mW, PNP Small Signal Transistor

FEATURES

- Low power loss, high efficiency
- Ideal for automated placement
- High surge current capability
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- On-board DC/DC converter

MECHANICAL DATA

• Case: SOT-23

• Molding compound meets UL 94 V-0 flammability rating

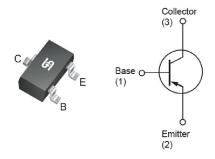
• Terminal: Matte tin plated leads, solderable per J-STD-002

• Meet JESD 201 class 1A whisker test

• Weight: 0.008g(approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
V _{CBO}	-40	V	
V_{CEO}	-40	V	
V_{EBO}	-5	V	
I _C	-200	mA	
h _{FE}	300		
Package	SOT-23		
Configuration	Single Die		





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	MMBT3906	UNIT
Marking code on the device		2A	
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current, dc	Ic	-200	mA
Power dissipation	P _D	350	mW
Junction temperature	T _J	-55 to +150	°C
Storage temperature	T _{STG}	-55 to +150	°C



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	TYP	UNIT
Junction-to-ambient thermal resistance	$R_{\Theta JA}$	357	°C/W

PARAMETER	CONDITIONS	SYMBOL	MIN	MAX	UNIT
Collector-base breakdown voltage	$I_C = -10 \mu A, I_E = 0$	V _{(BR)CBO}	-40	-	V
Collector-emitter breakdown voltage	$I_{\rm C}$ = -1 mA, $I_{\rm B}$ = 0	V _{(BR)CEO}	-40	-	V
Emitter-base breakdown voltage	$I_E = -10 \mu A, I_C = 0$	$V_{(BR)EBO}$	-5	-	V
Collector base cutoff current	V _{CB} = -40 V	I _{CBO}	-	-100	nA
Emitter base cutoff current	V _{EB} = -6 V	I _{EBO}	-	-50	nA
	$V_{CE} = -1 \text{ V}, I_{C} = -0.1 \text{ mA}$		60	300	
	V _{CE} = -1 V, I _C = -1 mA	_	80		
DC current gain	V _{CE} = -1 V, I _C = -10 mA	h _{FE}	100		
	$V_{CE} = -1 \text{ V}, I_{C} = -50 \text{ mA}$		60		
	V _{CE} = -1 V, I _C = -100 mA		30		
Collector-emitter saturation voltage	I _C = -10 mA, I _B = -1 mA	.,	-	-0.25	V
	$I_{\rm C}$ = -50 mA, $I_{\rm B}$ = -5 mA	$V_{CE(sat)}$	-	-0.4	
	I _C = -10 mA, I _B = -1 mA		-0.65	-0.85	V
Base-emitter saturation voltage	$I_{\rm C}$ = -50 mA, $I_{\rm B}$ = -5 mA	$V_{BE(sat)}$	-	-0.95	
Transition frequency	$V_{CE} = -20 \text{ V}$, $I_{C} = -10 \text{ mA}$, $f = 100 \text{MHz}$	f _⊤	250	-	MHz
Output capacitance	$f=1MHz$, $V_{CB} = -5 V$, $I_E = 0$	C _{OBO}	-	4.5	pF
Delay time	V_{CC} = -3V, V_{BE} = -0.5V, I_{C} = -10mA	t _d	-	35	ns
Rise time	I _{B1} = -1mA	t _r	-	35	ns
Storage time	V _{CC} = -3V, I _C = -10mA	t _s	-	225	ns
Fall time	I _{B1} = I _{B2} = -1mA	t _f	_	75	ns

ORDERING INFORMATION			
ORDERING CODE	PACKAGE	PACKING	
MMBT3906 RF	SOT-23	3K / 7" Reel	
MMBT3906 RFG	SOT-23	3K / 7" Reel	
MMBT3906 R5	SOT-23	10K / 13" Reel	
MMBT3906 R5G	SOT-23	10K / 13" Reel	

Note: "G" means green compound (halogen free)



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Capacitance

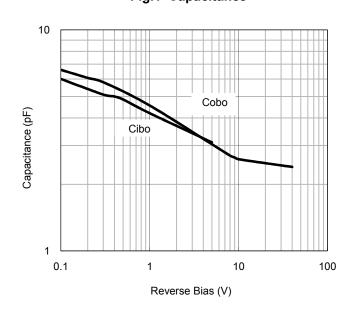


Fig.2 Charge Data

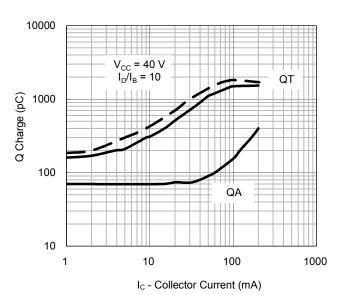


Fig.3 Turn - On Time

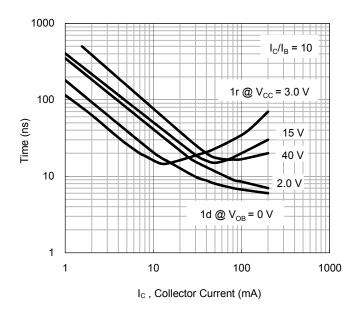
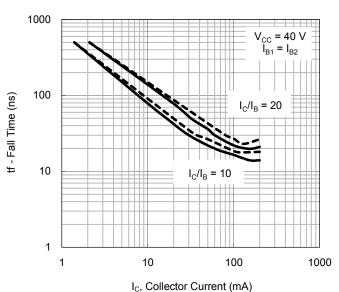


Fig.4 Fall Time





CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.5 Noise Figure VS. Frequency

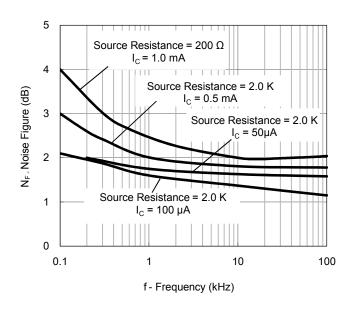


Fig.6 Noise Figure VS. Source Resistance

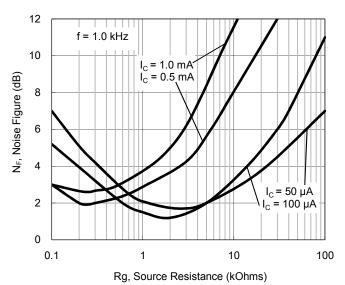


Fig.7 Current Gain

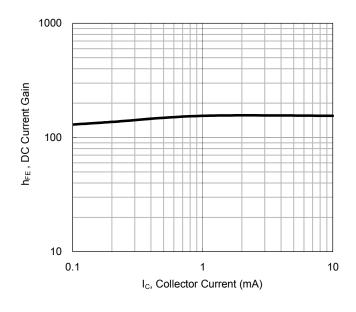
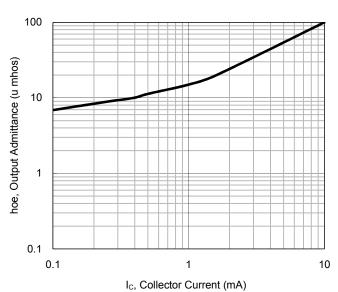


Fig.8 Output Admittance





CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.9 Input Impedance

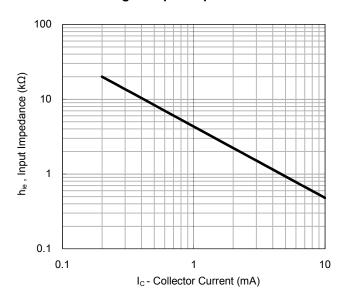


Fig.10 Voltage Feedback Ratio

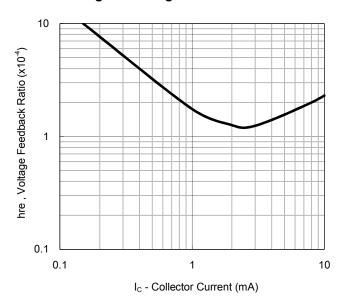


Fig.11 "ON" Voltages

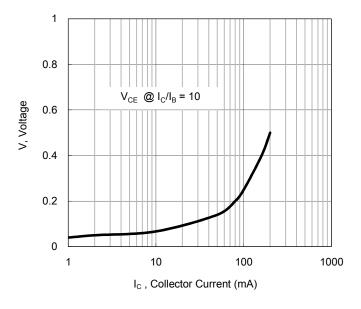
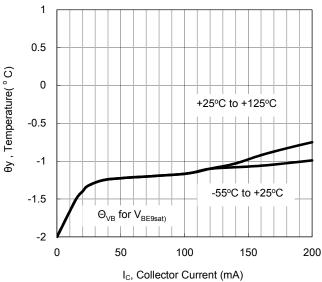


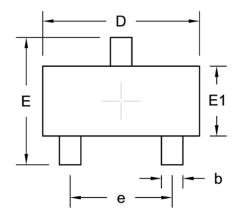
Fig.12 Temperature Coefficients

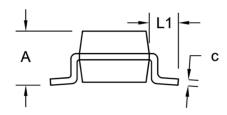




PACKAGE OUTLINE DIMENSION

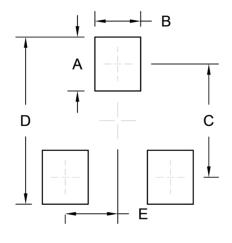
SOT-23





DIM.	Unit (mm)		Unit (inch)	
Dilvi.	Min.	Max.	Min.	Max.
Α	0.89	1.12	0.035	0.044
b	0.30	0.50	0.012	0.020
С	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
е	1.90	BSC	0.07	5 BSC
L1	0.54 REF.		0.021	REF.

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	1.00	0.039
В	0.85	0.033
С	2.10	0.083
D	3.10	0.122
Е	0.98	0.039



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